### TetraFET

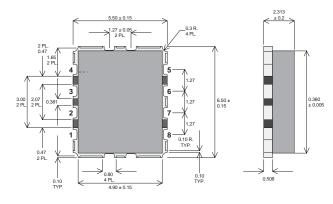
# D1031UK



## ROHS COMPLIANT METAL GATE RF SILICON FET

#### **MECHANICAL DATA**

Dimensions in mm.



#### F-0127 PACKAGE

PIN 1 – SOURCE
PIN 2 – DRAIN
PIN 3 – DRAIN
PIN 4 - SOURCE

PIN 5 – SOURCE PIN 6 – GATE PIN 7 – GATE PIN 8 – SOURCE

#### Ceramic Material: Alumina.

## GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 10W – 28V – 500MHz SINGLE ENDED

### FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- VERY LOW C<sub>rss</sub>
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN 13 dB MINIMUM

## **APPLICATIONS**

• HF/VHF/UHF COMMUNICATIONS from 1 MHz to 1 GHz

## ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C unless otherwise stated)

P <sub>D</sub>	Power Dissipation	30W
BV <sub>DSS</sub>	Drain – Source Breakdown Voltage	70V
BV <sub>GSS</sub>	Gate – Source Breakdown Voltage	±20V
I <sub>D(sat)</sub>	Drain Current	5A
T <sub>stg</sub>	Storage Temperature	–65 to 150℃
Тj	Maximum Operating Junction Temperature	200°C

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



#### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter		Test Conditions		Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source	V <sub>GS</sub> = 0	I <sub>D</sub> = 100mA	70			V
	Breakdown Voltage			70			v
I <sub>DSS</sub>	Zero Gate Voltage	V <sub>DS</sub> = 28V	/ V <sub>GS</sub> = 0			1	mA
	Drain Current					I	IIIA
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> = 20V	$V_{DS} = 0$			1	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage*	I <sub>D</sub> = 10mA	$V_{DS} = V_{GS}$	1		7	V
9 <sub>fs</sub>	Forward Transconductance*	V <sub>DS</sub> = 10V	I <sub>D</sub> = 1A	0.8			S
G <sub>PS</sub>	Common Source Power Gain	P <sub>O</sub> = 10W		13			dB
η	Drain Efficiency	V <sub>DS</sub> = 28V	I <sub>DQ</sub> = 0.1A	50			%
VSWR	Load Mismatch Tolerance	f = 500MHz		20:1			—
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 0V$	$V_{GS} = -5V f = 1MHz$			60	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 28V	$V_{GS} = 0$ f = 1MHz			30	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	V <sub>DS</sub> = 28V	$V_{GS} = 0$ f = 1MHz			2.5	pF

\* Pulse Test: Pulse Duration = 300  $\mu s$  , Duty Cycle  $\leq 2\%$ 

#### THERMAL DATA

R <sub>THi-case</sub>	Thermal Resistance Junction – Case	Max. 6℃ / W
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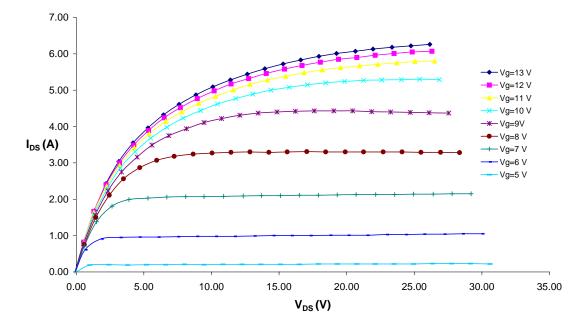
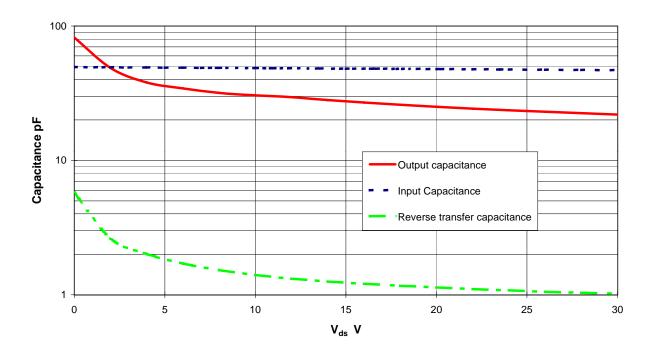


Figure 1 – Typical IV Characteristics.





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